

SUB  
C1  
CONT.

a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;

a first insulating film on top of the transistor;

a capacitor formed on the first insulating film, the capacitor having a dielectric film made of one of a ferroelectric material and a high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween; and

Control  
B1

a silicon oxide film residing on top of the capacitor to form a planarized surface;

wherein nitrogen resides over the planarized surface of the silicon oxide film; and

wherein the contact is positioned above the silicon nitride film including nitrogen.

SUB  
C2

5. (Twice Amended) A semiconductor device, comprising:

a contact;

a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;

B2

a first insulating film residing on top of the transistor;

a capacitor formed on the first insulating film, the capacitor having a dielectric made of one of ferroelectric material and a high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween;

a second insulating film formed on the capacitor;

a local interconnection formed on the second insulating film to electrically connecting the upper electrode of the capacitor with the first impurity region;

SUB  
C2  
CONT.

a third insulating film formed on the local interconnection and the second insulating film;  
a first wiring formed on the third insulating film and electrically connected to the second impurity region via a hole which is formed on the first insulating film, the second insulating film, and the third insulating film;

Cont'd  
B2

a fourth insulating film on top of the first wiring to serve an upper planarized surface, wherein nitrogen resides on top of the upper planarized surface of the fourth insulating film; wherein the contact is positioned above the silicon nitride film including nitrogen; and a second wiring formed on the fourth insulating film.

SUB  
C3

12. (Twice Amended) a semiconductor device, comprising:

a contact;

a transistor having a first impurity region and a second impurity region formed on a semiconductor substrate, and a gate electrode formed on the semiconductor substrate;

a first insulating film on top of the transistor;

a capacitor formed on the first insulating film, the capacitor having a dielectric film made of one of a ferroelectric material and a high-dielectric material, and an upper electrode and a lower electrode positioned to put the dielectric film therebetween;

a second insulating film on top of the capacitor to serve as an upper planarized surface;

wherein nitrogen resides on top of the upper planarized surface of the second insulating film;

and

wherein the contact is positioned above the silicon nitride film including nitrogen.